

INVERTER GRADE THYRISTORS

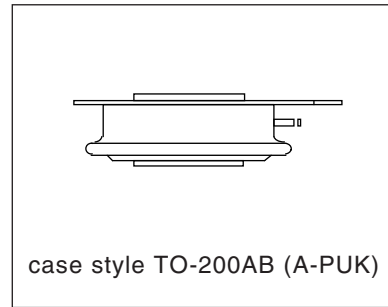
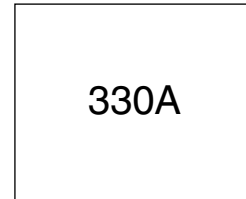
Hockey Puk Version

Features

- Metal case with ceramic insulator
- International standard case TO-200AB (A-PUK)
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- High surge current capability
- Low thermal impedance
- High speed performance

Typical Applications

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters



Major Ratings and Characteristics

Parameters	ST173C..C	Units
$I_{T(AV)}$	330	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	610	A
@ T_{hs}	25	°C
I_{TSM}	@ 50Hz 4680	A
	@ 60Hz 4900	A
I^2t	@ 50Hz 110	KA ² s
	@ 60Hz 100	KA ² s
V_{DRM}/V_{RRM}	1000 to 1200	V
t_q range	15 to 30	μs
T_J	- 40 to 125	°C

ST173C..C Series

Bulletin I25180 rev. B 04/00

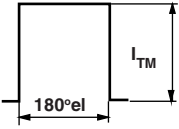
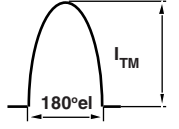
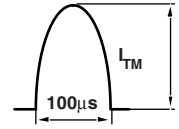
International
IR Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , maximum repetitive peak voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max. mA
ST173C..C	10	1000	1100	40
	12	1200	1300	

Current Carrying Capability

Frequency							Units
	760	660	1200	1030	5570	4920	
50Hz	760	660	1200	1030	5570	4920	A
400Hz	730	590	1260	1080	2800	2460	
1000Hz	600	490	1200	1030	1620	1390	
2500Hz	350	270	850	720	800	680	
Recovery voltage Vr	50	50	50	50	50	50	V
Voltage before turn-on Vd	V_{DRM}		V_{DRM}		V_{DRM}		
Rise of on-state current di/dt	50	50	-	-	-	-	A/µs
Heatsink temperature	40	55	40	55	40	55	°C
Equivalent values for RC circuit	47Ω / 0.22µF		47Ω / 0.22µF		47Ω / 0.22µF		

On-state Conduction

Parameter	ST173C..C	Units	Conditions	
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	330 (120)	A	180° conduction, half sine wave double side (single side) cooled	
	55 (85)	°C		
$I_{T(RMS)}$ Max. RMS on-state current	610	A	DC @ 25°C heatsink temperature double side cooled	
I_{TSM} Max. peak, one half cycle, non-repetitive surge current	4680		t = 10ms	No voltage reappplied
	4900		t = 8.3ms	reappplied
	3940		t = 10ms	100% V_{RRM}
	4120	t = 8.3ms	reappplied	
I^2t Maximum I^2t for fusing	110	KA ² s	t = 10ms	No voltage reappplied
	100		t = 8.3ms	reappplied
	77		t = 10ms	100% V_{RRM}
	71		t = 8.3ms	reappplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	1100	KA ² √s	t = 0.1 to 10ms, no voltage reappplied	

On-state Conduction

Parameter	ST173C..C	Units	Conditions
V_{TM} Max. peak on-state voltage	2.07	V	$I_{TM} = 600A, T_J = T_J \text{ max}, t_p = 10\text{ms sine wave pulse}$
$V_{T(TO)1}$ Low level value of threshold voltage	1.55		$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}, T_J = T_J \text{ max.}$
$V_{T(TO)2}$ High level value of threshold voltage	1.61		$(I > \pi \times I_{T(AV)}, T_J = T_J \text{ max.}$
r_{t1} Low level value of forward slope resistance	0.87	m Ω	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}, T_J = T_J \text{ max.}$
r_{t2} High level value of forward slope resistance	0.77		$(I > \pi \times I_{T(AV)}, T_J = T_J \text{ max.}$
I_H Maximum holding current	600	mA	$T_J = 25^\circ\text{C}, I_T > 30A$
I_L Typical latching current	1000		$T_J = 25^\circ\text{C}, V_A = 12V, R_a = 6\Omega, I_G = 1A$

Switching

Parameter	ST173C..C	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/ μs	$T_J = T_J \text{ max}, V_{DRM} = \text{rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$
t_d Typical delay time	1.1	μs	$T_J = 25^\circ\text{C}, V_{DM} = \text{rated } V_{DRM}, I_{TM} = 50A \text{ DC}, t_p = 1\mu\text{s}$ Resistive load, Gate pulse: 10V, 5 Ω source
t_q Max. turn-off time	Min 15 Max 30		$T_J = T_J \text{ max}, I_{TM} = 300A, \text{commutating } di/dt = 20A/\mu\text{s}$ $V_R = 50V, t_p = 500\mu\text{s}, dv/dt: \text{ see table in device code}$

Blocking

Parameter	ST173C..C	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μs	$T_J = T_J \text{ max. linear to } 80\% V_{DRM}, \text{ higher value available on request}$
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	40	mA	$T_J = T_J \text{ max, rated } V_{DRM}/V_{RRM} \text{ applied}$

Triggering

Parameter	ST173C..C	Units	Conditions
P_{GM} Maximum peak gate power	60	W	$T_J = T_J \text{ max}, f = 50\text{Hz}, d\% = 50$
$P_{G(AV)}$ Maximum average gate power	10		
I_{GM} Max. peak positive gate current	10	A	$T_J = T_J \text{ max}, t_p \leq 5\text{ms}$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J \text{ max}, t_p \leq 5\text{ms}$
$-V_{GM}$ Maximum peak negative gate voltage	5		
I_{GT} Max. DC gate current required to trigger	200	mA	$T_J = 25^\circ\text{C}, V_A = 12V, R_a = 6\Omega$
V_{GT} Max. DC gate voltage required to trigger	3	V	
I_{GD} Max. DC gate current not to trigger	20	mA	$T_J = T_J \text{ max, rated } V_{DRM} \text{ applied}$
V_{GD} Max. DC gate voltage not to trigger	0.25	V	

Outline Table

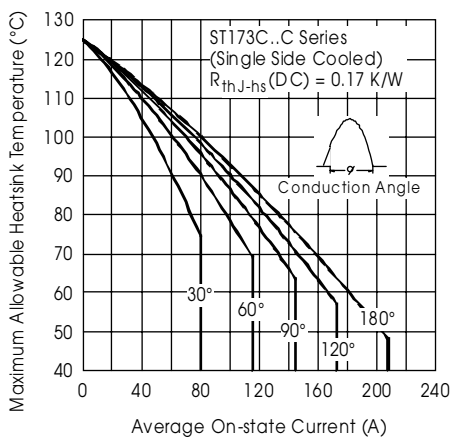
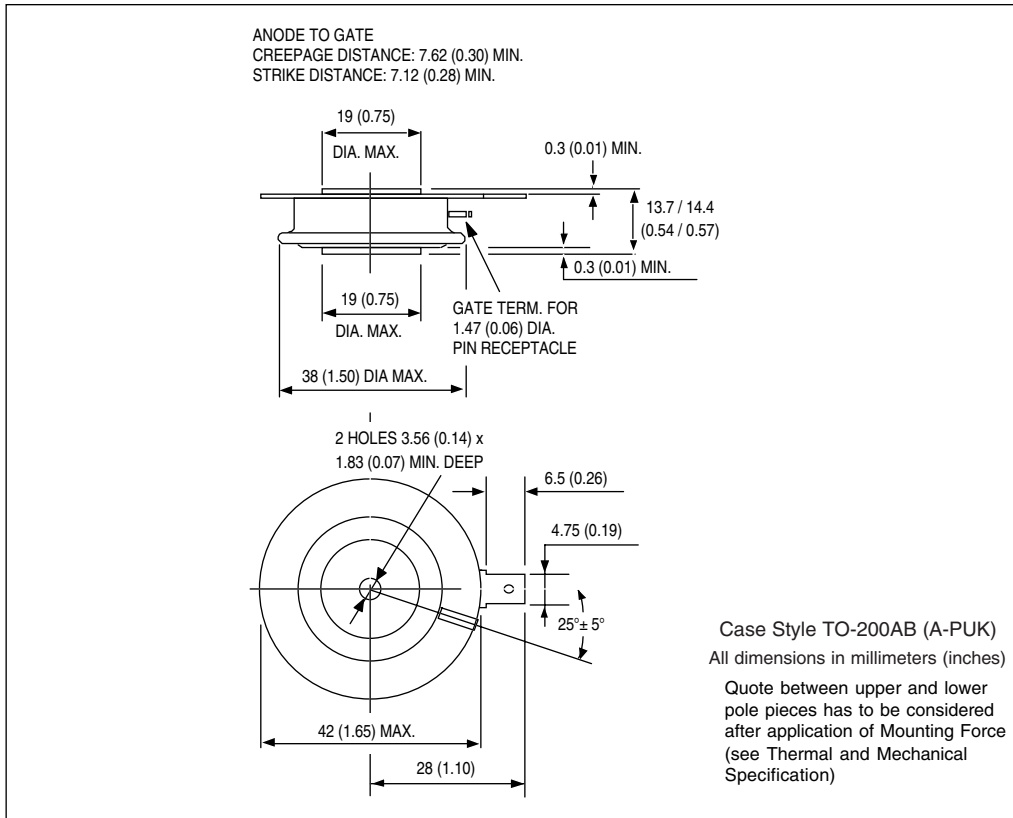


Fig. 1 - Current Ratings Characteristics

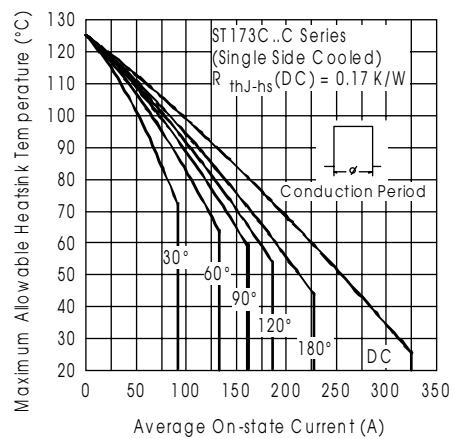


Fig. 2 - Current Ratings Characteristics

ST173C..C Series

Bulletin I25180 rev. B 04/00

International
IRF Rectifier

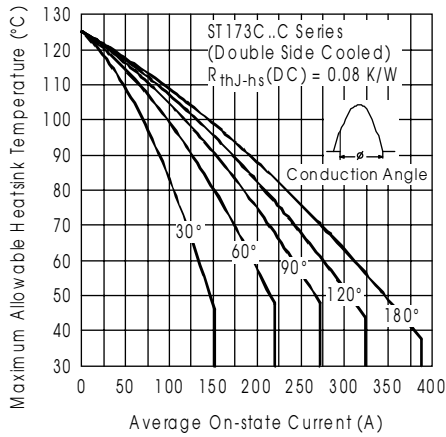


Fig. 3 - Current Ratings Characteristics

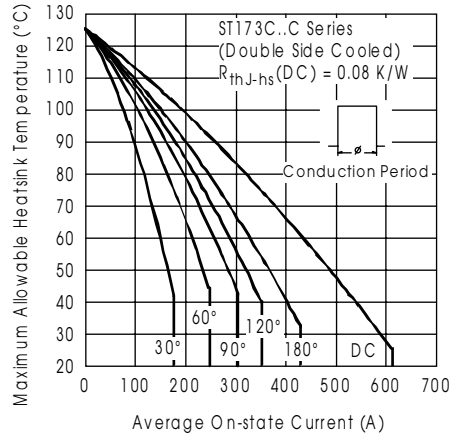


Fig. 4 - Current Ratings Characteristics

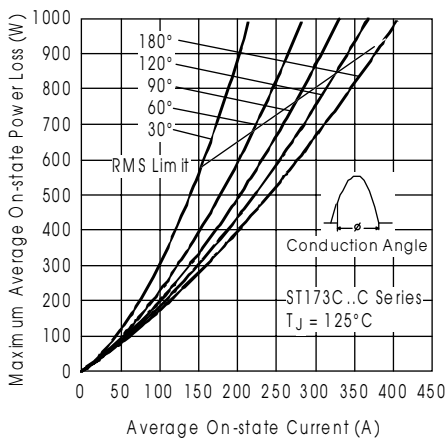


Fig. 5 - On-state Power Loss Characteristics

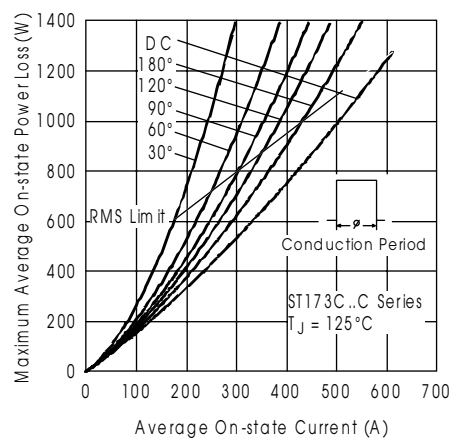


Fig. 6 - On-state Power Loss Characteristics

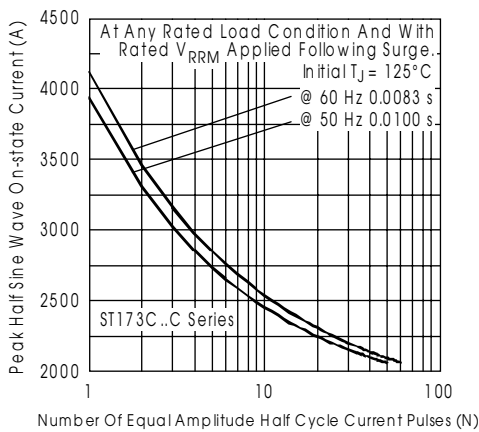


Fig. 7 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

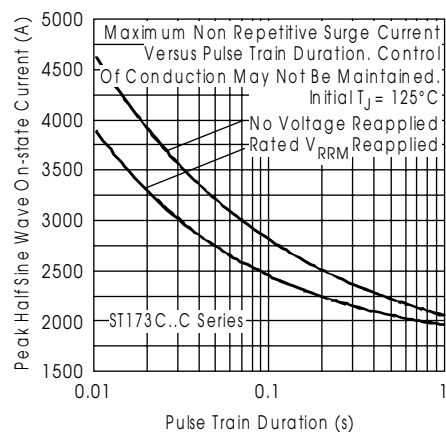


Fig. 8 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

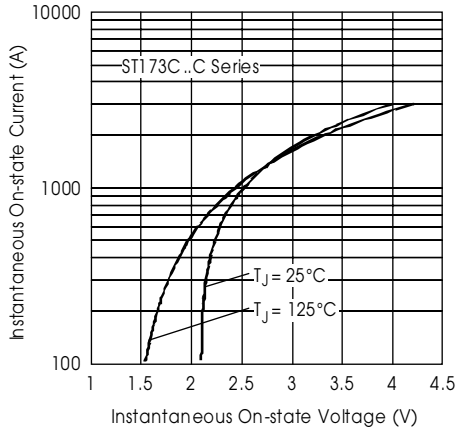


Fig. 9 - On-state Voltage Drop Characteristics

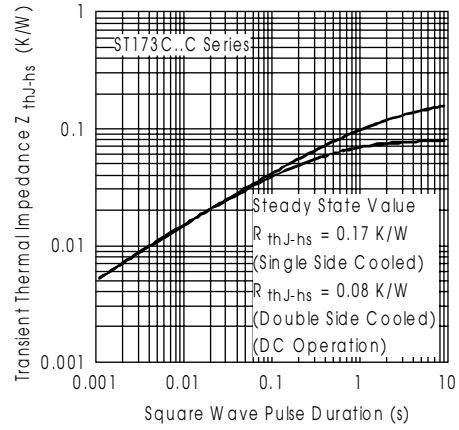


Fig. 10 - Thermal Impedance Z_{thj-hs} Characteristics

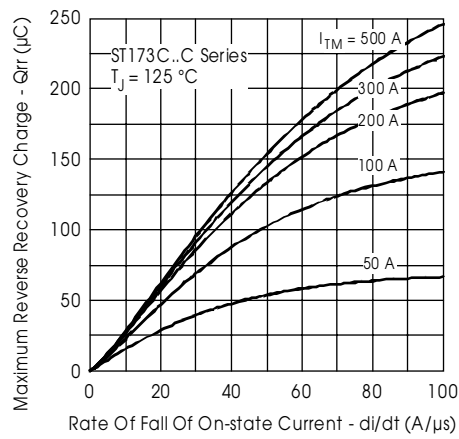


Fig. 11 - Reverse Recovered Charge Characteristics

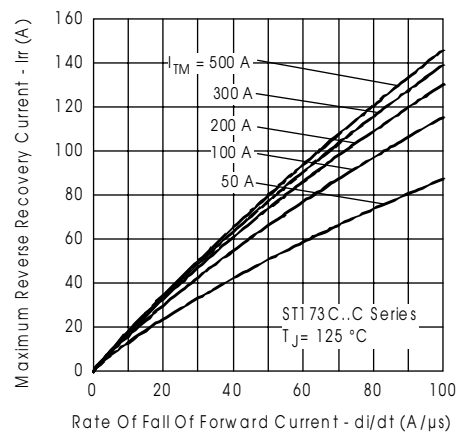


Fig. 12 - Reverse Recovery Current Characteristics

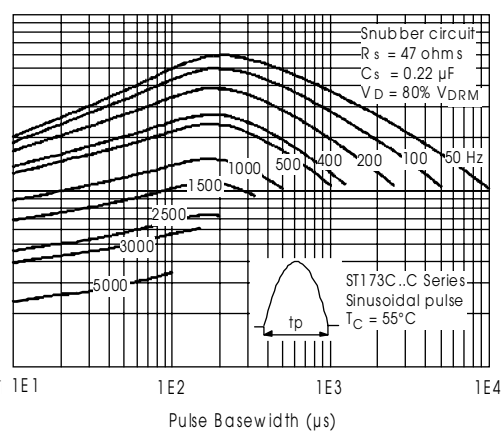
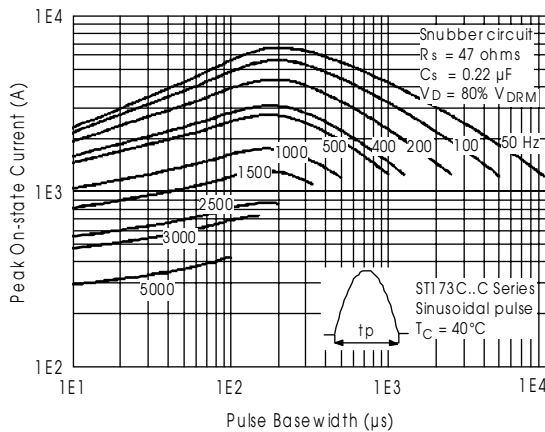


Fig. 13 - Frequency Characteristics

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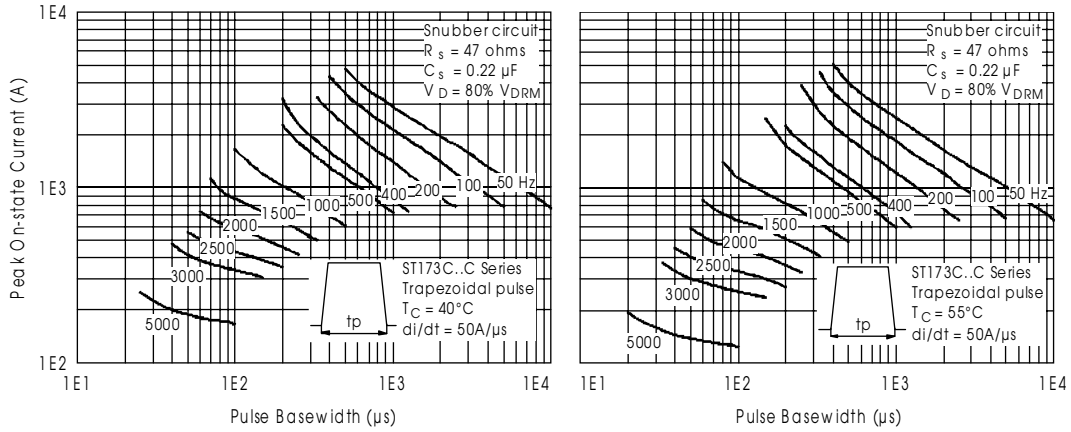


Fig. 14 - Frequency Characteristics

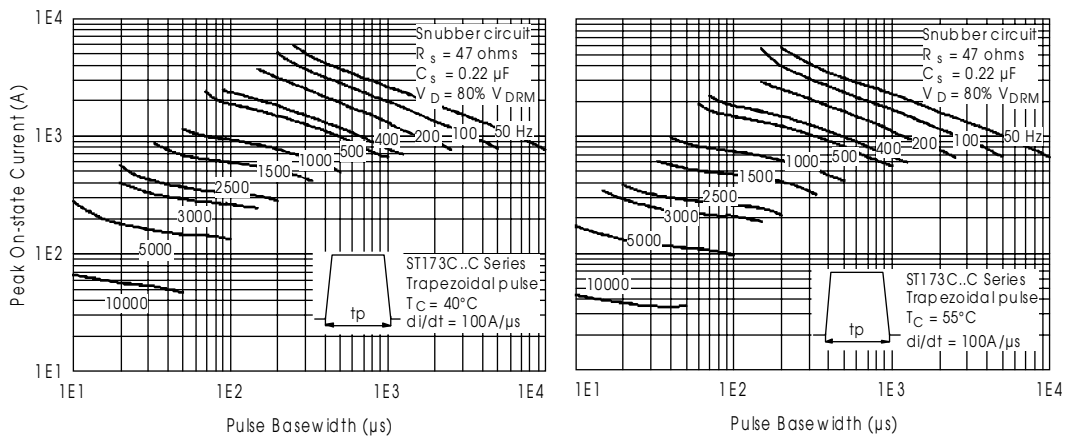


Fig. 15 - Frequency Characteristics

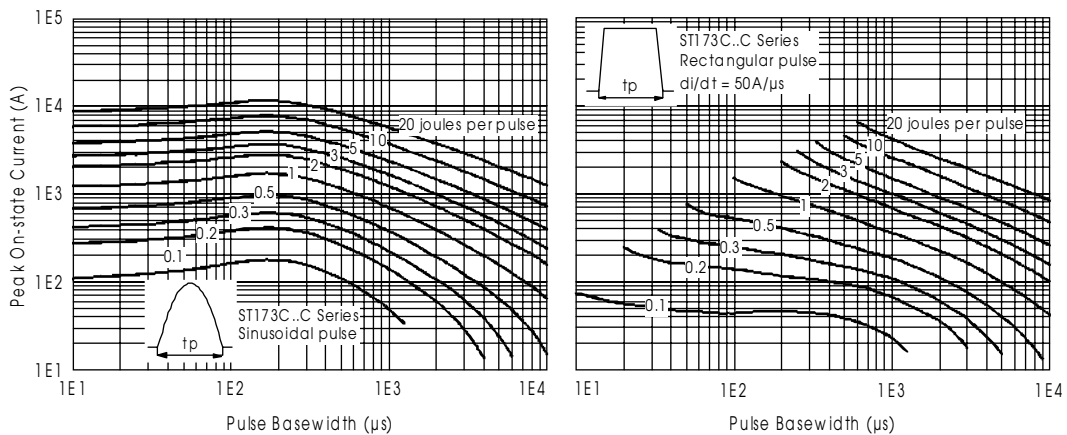


Fig. 16 - Maximum On-state Energy Power Loss Characteristics

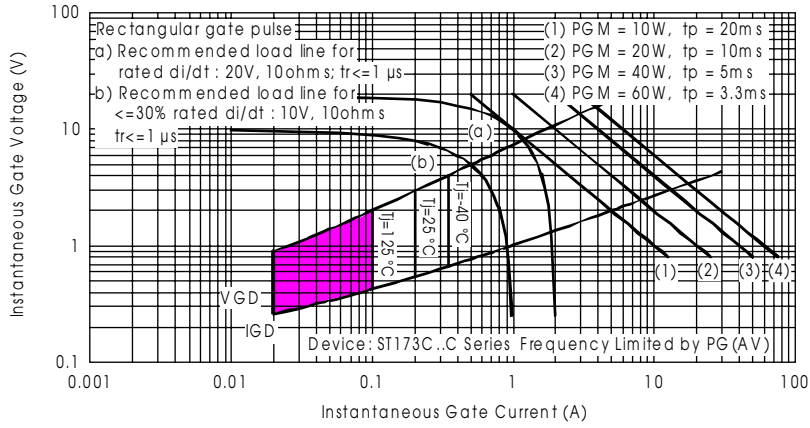


Fig. 17 - Gate Characteristics